

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

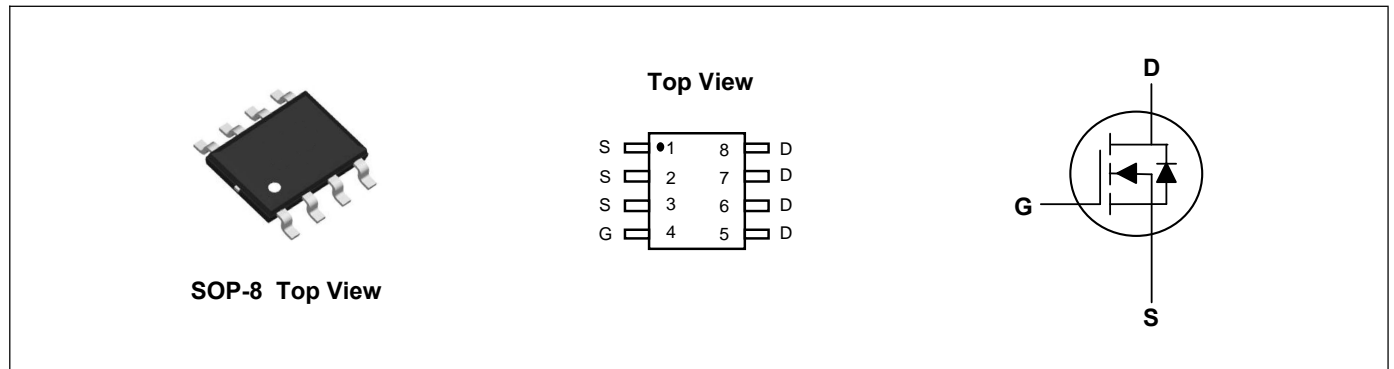
Applications

- High Frequency Point-of-Load, Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch

Product Summary



V_{DS}	80	V
I_D	14	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	7	m Ω



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$I_D@T_A=25^\circ\text{C}$	14	A
Continuous Drain Current ¹	$I_D@T_A=70^\circ\text{C}$	9.8	A
Pulsed Drain Current ²	I_{DM}	48	A
Single Pulse Avalanche Energy ³	E_{AS}	125	mJ
Total Power Dissipation ⁴	$P_D@T_A=25^\circ\text{C}$	2	W
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	62.5	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	80	---	---	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =12A	---	5.8	7	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	2.0	3.0	4.0	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =3A	---	10	---	S
Gate Resistance	R _g	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.1	---	Ω
Total Gate Charge	Q _g	V _{DS} =40V, V _{GS} =10V, I _D =10A	---	31	---	nC
Gate-Source Charge	Q _{gs}		---	4	---	
Gate-Drain Charge	Q _{gd}		---	9	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =40V, V _{GS} =10V, R _G =6Ω, I _D =8A	---	22	---	ns
Rise Time	T _r		---	16	---	
Turn-Off Delay Time	T _{d(off)}		---	40	---	
Fall Time	T _f		---	30	---	
Input Capacitance	C _{iss}	V _{DS} =40V, V _{GS} =0V, f=1MHz	---	1710	---	pF
Output Capacitance	C _{oss}		---	330	---	
Reverse Transfer Capacitance	C _{rss}		---	10	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ¹	I _S	T _C =25°C	---	---	14	A
Pulsed Source Current ²	I _{SM}		---	---	48	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
Reverse Recovery Time	t _{rr}	I _S =10A, V _R =30V di/dt=100A/μs, T _J =25°C	---	35	---	nS
Reverse Recovery Charge	Q _{rr}		---	33	---	nC

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH
- 4.The power dissipation is limited by 150°C junction temperature

Typical Characteristics

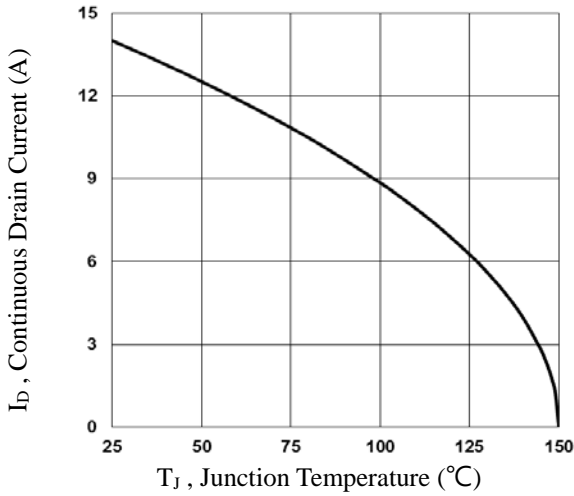


Fig.1 Continuous Drain Current vs. T_J

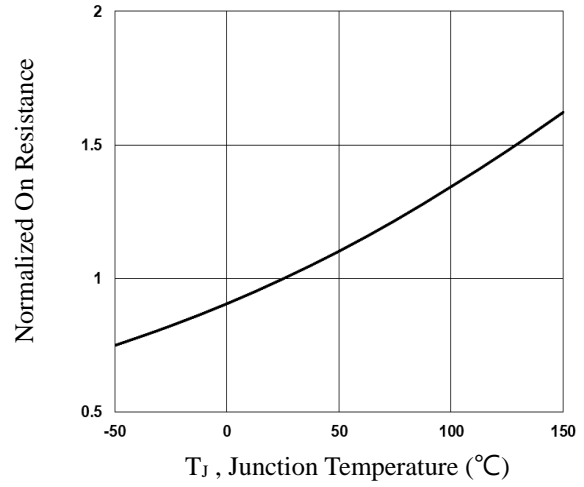


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

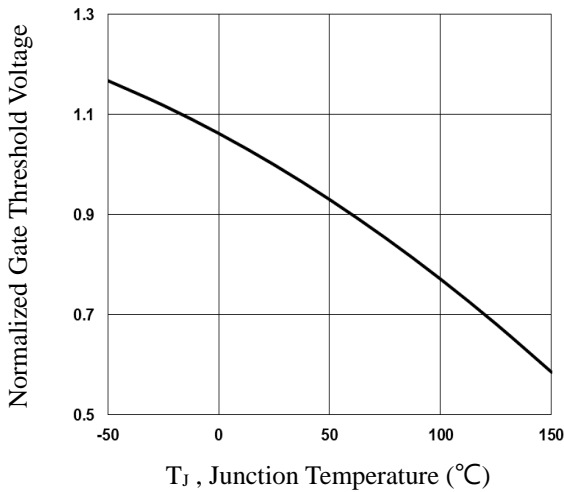


Fig.3 Normalized V_{th} vs. T_J

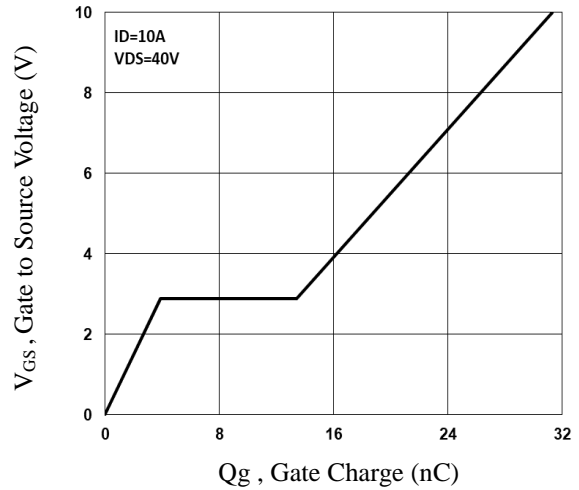


Fig.4 Gate Charge Characteristics

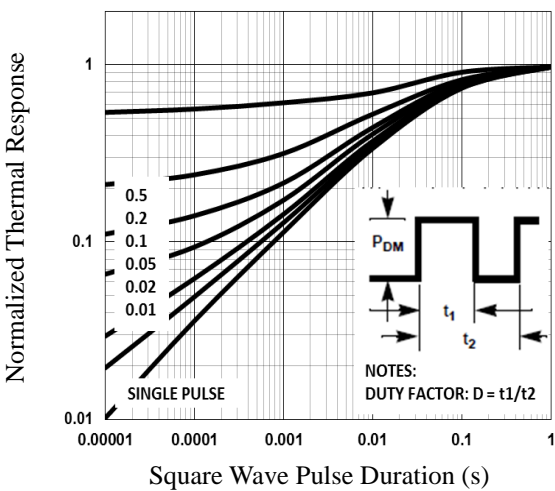


Fig.5 Normalized Transient Impedance

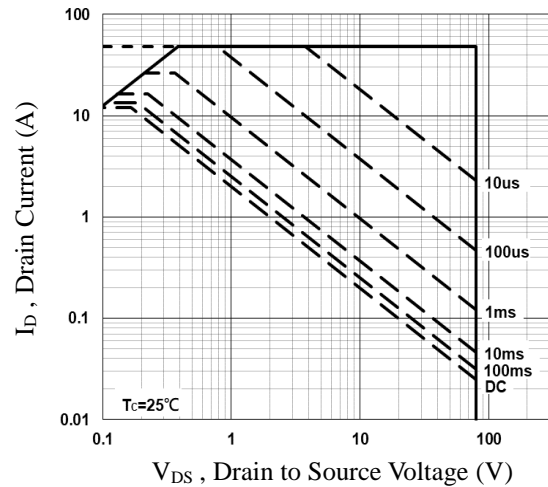


Fig.6 Maximum Safe Operation Area

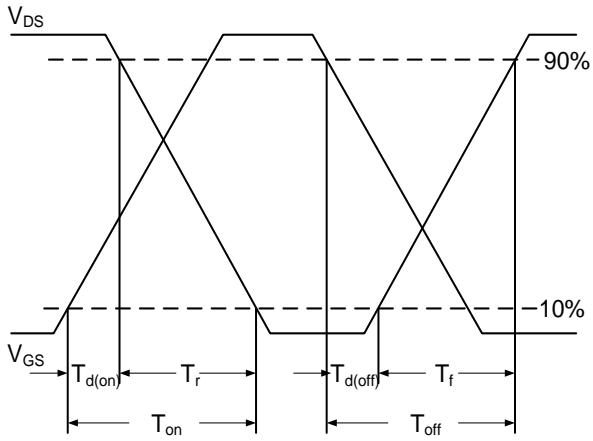


Fig.7 Switching Time Waveform

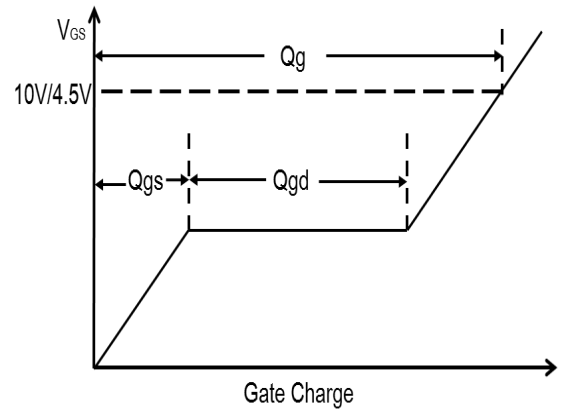


Fig.8 Gate Charge Waveform

SOP-8 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	1.35	1.55	1.75	A₁	0.10	0.18	0.25
A₂	1.25	1.45	1.65	A₃	--	0.25	--
b_p	0.36	0.42	0.51	c	0.19	0.22	0.25
D	4.70	4.92	5.10	E	3.80	3.90	4.00
e	--	1.27	--	H_E	5.80	6.00	6.20
L	--	1.05	--	L_p	0.40	0.68	1.00
Q	0.60	0.65	0.73	v	--	0.25	--
w	--	0.25	--	y	--	0.10	--
Z	0.30	0.50	0.70	θ	0°		8°